

## Super Barrier Rectifier TM

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
$I_{F(AV)}$ Rectangular Waveform	10	А
V <sub>RRM</sub>	60	V
V <sub>F</sub> @5A, Tj=125 <sup>0</sup> C	0.54	V, typ
Tj (operating/storage)	-65 to 150	°C

ELECTRICAL:

- \* Low Forward Voltage Drop
- \* Reliable High Temperature Operation
- \* Super Barrier Design
- \* Softest, fast switching capability
- \* 150°C Operating Junction Temperature

Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

MECHANICAL:

\* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages

Case Styles					
SBR1060CT	SBR1060CTF	SBR1060CTI	SBR1060CTB		
			Sec.		
Anode Common 3 Anode Anode	Anode Common 3 Anode Anode	Anode Common 3 Anode Anode	2 Common Anode 1 Cathode Anode		
TO-220AB	ITO-220	TO-262	TO-263		



Maximum Ratings and Electrical Cha	racteristics						
(at 25 <sup>o</sup> C unless otherwise specified)							
	SYMBOL			UNITS			
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V <sub>rm</sub> V <sub>rwm</sub> V <sub>rrm</sub>	60		Volts			
Average Rectified Forward Current (Rated V <sub>R</sub> -20Khz Square Wave) - 50% duty cycle	Io	10		Amps			
Peak Forward Surge Current - 1/2 60hz	I <sub>FSM</sub>	120		Amps			
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I <sub>RRM</sub>	2		Amps			
Instantaneous Forward Voltage (per leg) I <sub>F</sub> = 5A; T <sub>J</sub> = 25°C I <sub>F</sub> = 5A; T <sub>J</sub> = 125°C	V <sub>F</sub>	Тур  	Max 0.68 0.57	Volts			
Maximum Instantaneous Reverse Current at Rated $V_{RM}$ T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	I <sub>R</sub> .	Тур  	Max 0.5 100	mA mA			
Maximum Rate of Voltage Change (at Rated $V_R$ )	dv/dt	10,000		V/uS			
Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263 Package = ITO-220	Rθ <sub>Jc</sub>	2 4		°C/W			
Operating and Storage Junction Temperature	TJ	-65 to +150		°C			

\* Pulse width < 300 uS, Duty cycle < 2%

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